

2811

Patent
Attorney's Docket No. 030681-280

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Sung-nam LEE et al.) Group Art Unit: 2811
Application No.: 09/776,846) Examiner: Sara Crane
Filed: February 6, 2001) Confirmation No.: 6862
For: NITRIDE SEMICONDUCTOR LIGHT)
EMITTING DEVICE)

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**INFORMATION DISCLOSURE STATEMENT
TRANSMITTAL LETTER**

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Enclosed is an Information Disclosure Statement and accompanying form PTO-1449 for the above-identified patent application.

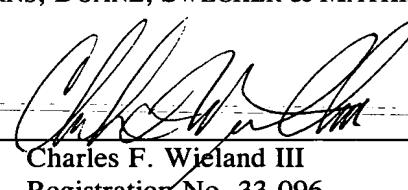
- No additional fee for submission of an IDS is required.
- The fee of \$180.00 (1806) as set forth in 37 C.F.R. § 1.17(p) is also enclosed.
- A statement under 37 C.F.R. § 1.97(e) is also enclosed.
- A statement under 37 C.F.R. § 1.97(e), and the fee of \$180.00 (1806) as set forth in 37 C.F.R. § 1.17(p) are also enclosed.
- Charge \$_____ to Deposit Account No. 02-4800 for the fee due.
- A check in the amount of \$_____ is enclosed for the fee due.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17 and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

By:


Charles F. Wieland III
Registration No. 33,096

P.O. Box 1404
Alexandria, Virginia 22313-1404
(703) 836-6620

Date: February 20, 2003



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3-31-03
Refiled

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**FIRST
INFORMATION DISCLOSURE STATEMENT**

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. § 1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98.

Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

I, the undersigned, hereby state that each item of information contained in this Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.

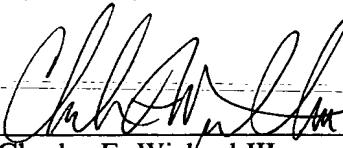
This Information Disclosure Statement contains information which is not in the English language but was cited in a search report or other action by a foreign patent office in a counterpart foreign application. In accordance with M.P.E.P. § 609A(3) an English language version of the search report or action which indicates the degree of relevance found by the foreign office is being submitted herewith.

To assist the Examiner, the document is listed on the attached form PTO-1449. It is respectfully requested that an Examiner-initialed copy of this form be returned to the undersigned.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

Date: February 20, 2003

By: 

Charles F. Wieland III
Registration No. 33,096

P.O. Box 1404
Alexandria, Virginia 22313-1404
(703) 836-6620

NOTICE TO SUBMIT RESPONSE

Patent Applicant

Name: Samsung Electro-mechanics Co., Ltd.
(Applicant Code: 119980018064)
Address: 314 Maetan-3-dong, Paldal-gu, Suwon-City,
Kyunggi-do, Korea

Attorney

Name: Young-pil Lee et al.
Address: 2F Cheonghwa Bldg., 1571-18 Seocho-dong, Seocho-ku, Seoul,
Korea

Application No.: 10-2001-0001550

Title of the Invention: Nitride semiconductor light emitting device

According to Article 63 of the Korean Patent Law, the applicant is notified that the present application has been rejected for the reasons given below. Any Argument or Amendment which the applicant may wish to submit, must be submitted by February 20, 2003. An indefinite number of one-month extensions in the period for submitting a response may be obtained upon request, however no official confirmation of the acceptance of a request for an extension will be issued.

Reasons

The invention as claimed in claims 1 through 22 could have been easily invented by one of ordinary skill in the art prior to the filing of the application, and thus this application is rejected according to Article 29(2) of the Korean Patent Law.

Below

The present invention relates to a nitride semiconductor light emitting device in which multi-quantum barrier layers consisting of AlGaN/GaN, AlGaN/InGaN, or AlGaN/AlGaN are formed at one side of an active layer. However, International Patent Laid-open Publication No. WO99/46822 (published on September 16, 1999) set forth herein discloses a nitride semiconductor device in which a supper lattice multiple layer consisting of

AlGaN/GaN, AlGaN/InGaN, or AlGaN/AlGaN is formed at a p-type side or an n-type side of an active layer. Accordingly, the present invention is considered to have been possibly invented by one skilled in the art based on the cited invention.

Enclosure: International Patent Laid-open Publication No. WO00/46822

20 December 2002

Dong-yup Kim/Examiner
Examination Division 4
Korean Industrial Property Office